

before forming the surface resin layer.

A²
7. (Amended) A method for manufacturing a semiconductor device as claimed in claim 5, further comprising
a surface grinding step of exposing the projection electrodes from the surface resin layer by polishing or grinding the surface resin layer.

A³
9. (Amended) A method for manufacturing a semiconductor device as claimed in claim 3, in which the surface resin layer and the back side resin layer are so formed as to have substantially the same thicknesses respectively.

A⁴
12. (Amended) A semiconductor device as claimed in claim 10, in which the semiconductor chip is bonded face-down onto the solid device with an active surface of the semiconductor chip opposed to the solid device.

A⁵
15. (Amended) A semiconductor device as claimed in claim 13, in which the substrate is provided with through holes enabling the electrical connection from a back side of the substrate to base portions of the projection electrodes.

A⁶
20. (Amended) A method for manufacturing a semiconductor device as claimed in claim 17, in which a back side of the semiconductor substrate or an inactive surface side of the semiconductor chip is polished or ground before the cutting out step.

21. (Amended) A method for manufacturing a semiconductor device as claimed in claim 17, in which the projection electrodes are formed to be higher than the active surface of the semiconductor chip and lower than an inactive surface of the semiconductor chip.

A⁷
24. (Amended) A method for manufacturing a semiconductor device as claimed in claim 22, further comprising a step of forming through holes enabling an electrical connection from a back side of the substrate to base portions of the projection electrodes.